

Supplementary Information for:

**Atomically flat and thermally stable graphene on Si(111) with preserved intrinsic
electronic properties**

Xiaoxia Li,^{‡ab} Bin Li,^{‡a} Xiaodong Fan,^{ab} Laiming Wei,^{*ab} Lin Li,^{ab} Ran Tao,^{ab}
Xiaoqiang Zhang,^{ab} Hui Zhang,^{ab} Qiang Zhang,^{ab} Hongbin Zhu,^{ab} Shengbai Zhang,^{ac}
Zhenyu Zhang,^a and Changgan Zeng^{*ab}

^a *International Center for Quantum Design of Functional Materials (ICQD), Hefei National Laboratory for Physical Sciences at the Microscale, and Synergetic Innovation Center of Quantum Information and Quantum Physics, University of Science and Technology of China, Hefei, Anhui 230026, China*

^b *CAS Key Laboratory of Strongly-Coupled Quantum Matter Physics, and Department of Physics, University of Science and Technology of China, Hefei, Anhui 230026, China*

^c *Department of Physics, Applied Physics and Astronomy, Rensselaer Polytechnic Institute, Troy, New York 12180, USA*

[‡]These authors contributed equally to this work.

^{*}Corresponding authors. E-mail: cgzeng@ustc.edu.cn, laiming@ustc.edu.cn

Supplemental figure

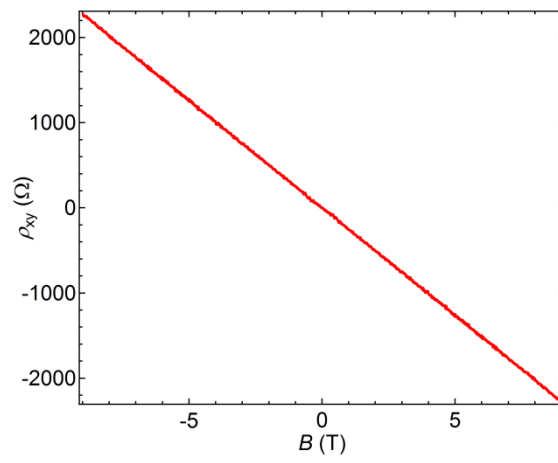


Fig. S1. Hall resistivity ρ_{xy} as a function of the magnetic field B at 1.5 K for the graphene/Si device shown in Fig. 5 of the main text.